

“HALF-BRIDGE” IGBT

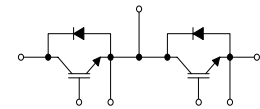
V_{CES} = 1200V
I_c = 100A
V_{CE(ON)} typ. = 1.7V
@I_c = 100A

Feature

- IGBT New Technology
- Low V_{CE} (sat)
- Low Turn-off losses
- Short tail current
- Positive temperature coefficient

Application

- AC & DC Motor controls
- General purpose inverters
- Optimized for high current inverter
- Servo Controls
- UPS, Robotics



Package : V1

Absolute Maximum Ratings @ T_j=25°C (Per Leg)

Symbol	Parameter	Condition	Ratings	Unit
V _{CES}	Collector-to-Emitter Voltage	V _{GE} = 0V, I _c = 250μA	1200	V
V _{GE}	Gate emitter voltage		± 20	V
I _c	Continuous Collector Current	T _c = 80°C (25°C)	100 (140)	A
I _{CP}	Pulsed collector current	T _c = 25°C	200	A
I _F	Diode Continuous Forward Current	T _c = 80°C (25°C)	100 (140)	A
I _{FM}	Diode Maximum Forward Current	T _c = 25°C	200	A
V _{iso}	Isolation Voltage test	AC @ 1 minute	2500	V
Weight	Weight of Module		190	G
T _j	Junction Temperature		-40 ~ 150	°C
T _{stg}	Storage Temperature		-40 ~ 125	°C
Md	Mounting torque with screw M5		2.0	N.m
	Terminal connection torque		2.0	N.m

Static Characteristics @ T_j = 25°C (unless otherwise specified)

Parameters		Min	Typ	Max	Unit	Test conditions
V _{(BR)CES}	Collector-to-Emitter Breakdown Voltage	1200	—	—	V	V _{GE} = 0V, I _c = 2mA
V _{CE(ON)}	Collector-to-Emitter Saturation Voltage	1.4	1.7	2.1		I _c = 100A, V _{GE} = 15V
V _{GE(th)}	Gate Threshold Voltage	5.0	5.8	6.5		V _{CE} = V _{GE} , I _c = 2mA
I _{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	V _{GE} = 0V, V _{CE} = 1200V
I _{GES}	Gate-to-Emitter Leakage Current	—	—	400	nA	V _{CE} = 0V, V _{GE} = 20V
V _f	Forward voltage drop	1.4	1.7	2.1	V	I _F = 100A
R _{GINT}	Integrated gate resistor	—	7.5	—	Ω	

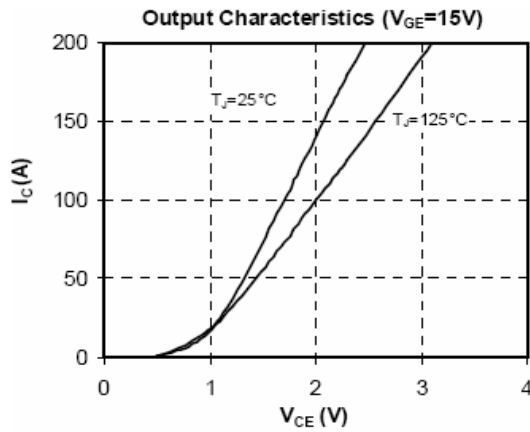
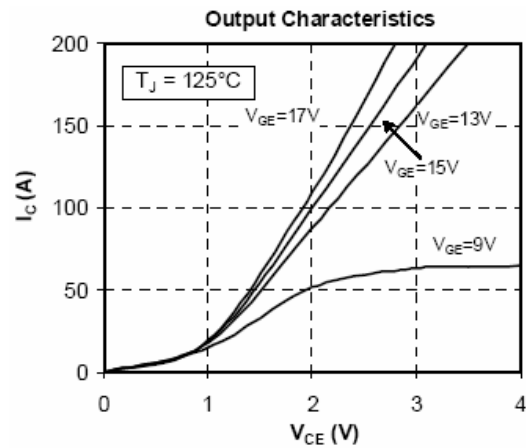
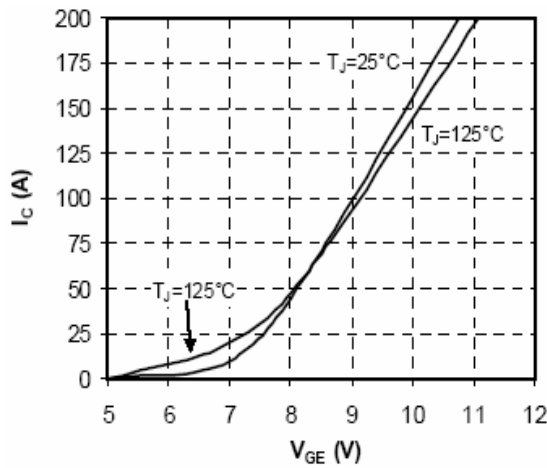
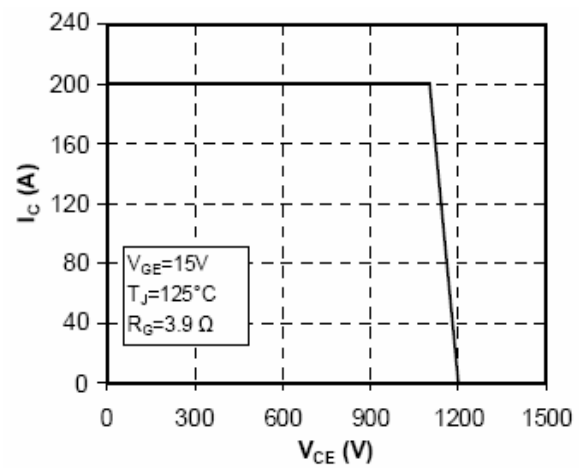
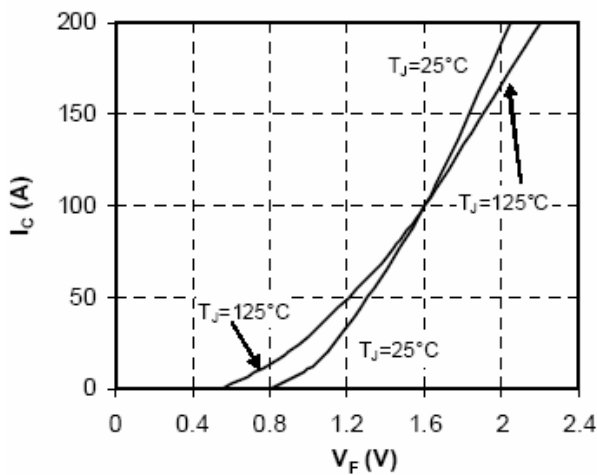
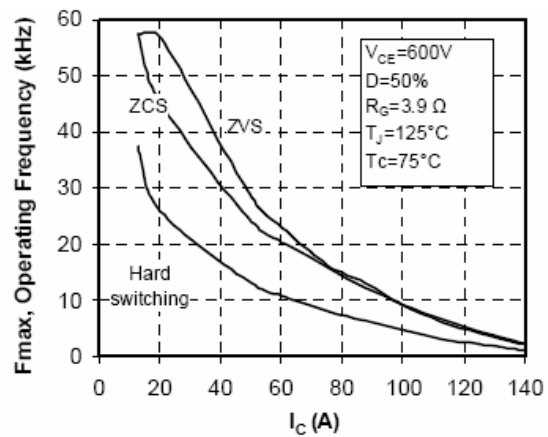
Electrical Characteristic Values (IGBT / DIODE) @ $T_j = 25^\circ\text{C}$ (unless otherwise specified)

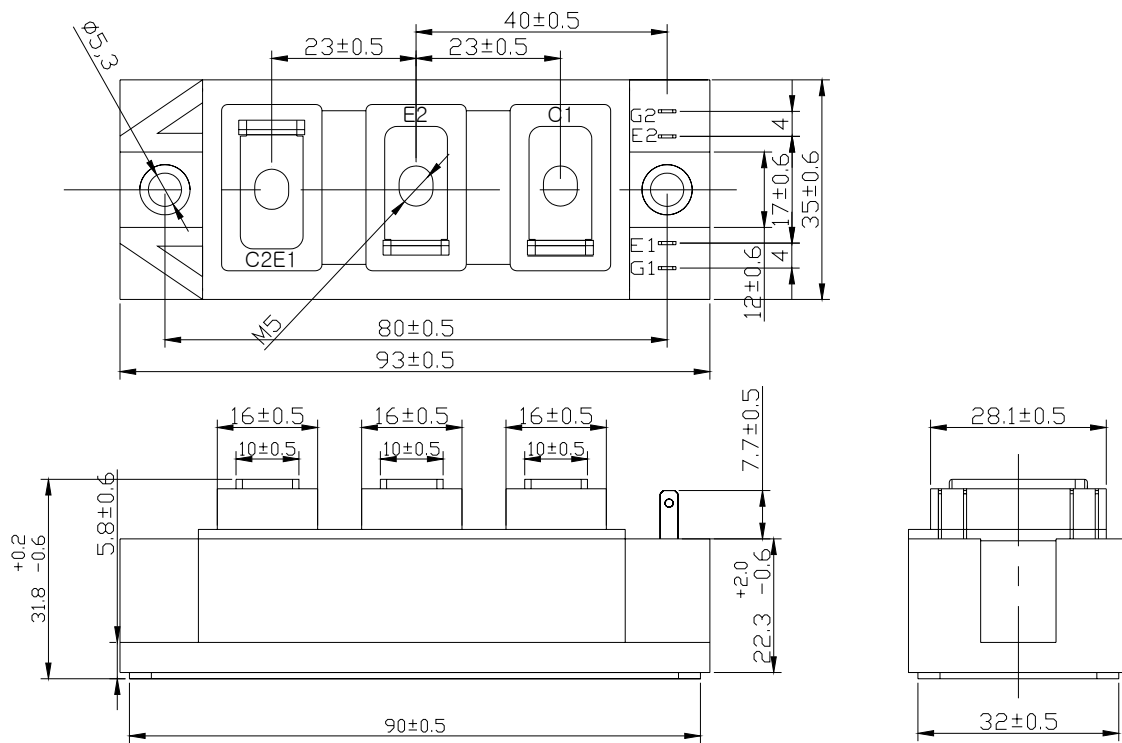
Parameters		Min	Typ	Max	Unit	Test conditions
C_{iss}	Input capacitance	—	7200	—	pF	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$ $f = 1\text{ MHz}$
C_{oss}	Output capacitance	—	400	—		
C_{rss}	Reverse transfer capacitance	—	300	—		
$t_{d(on)}$	Turn-on delay time	—	290	—	ns	$T_j = 125^\circ\text{C}$, $V_{CC} = 600\text{V}$ $I_C = 100\text{A}$, $V_{GE} = \pm 15\text{V}$ $R_G = 3.9\Omega$
t_r	Rise time	—	50	—		
$t_{d(off)}$	Turn-off delay time	—	590	—		
t_f	Fall time	—	90	—		
V_{BR}	Cathode-Anode breakdown Voltage	1200	—	—	V	$I_R = 250\mu\text{A}$
I_{RM}	Maximum Reverse Leakage Current	—	—	250	μA	$V_R = 1200\text{V}$
t_{rr}	Reverse Recovery Time	—	170	—	ns	$I_F = 100\text{A}$, $V_R = 600\text{V}$
Q_{rr}	Reverse Recovery Charge	—	9	—	μC	$di / dt = 2000\text{A} / \mu\text{s}$

Thermal Characteristics

Symbol	Parameter	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction-to-Case (IGBT Part, Per 1/2 Module)	-	-	0.26	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Junction-to-Case (Diode Part, Per 1/2 Module)	-	-	0.48	
$R_{\theta CS}$	Case-to-Heat Sink (Conductive grease applied)	-	0.05	-	

※ Data and specifications subject to change without notice.


Fig 1. Typ. IGBT Output Characteristics

Fig 2. Typ. IGBT Out Characteristics

Fig 3. Typ. Transfer Characteristics

Fig 4. Reverse Bias Operating Area

Fig 5. Forward Characteristics of Diode

Fig 6. Operating Frequency vs Collector Current

Package Outline (dimensions in mm)


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May 2006